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(54) **SEMICONDUCTOR DEVICE INCLUDING PROTECTION STRUCTURE AND MANUFACTURING METHOD THEREFOR**

(57) An embodiment of a semiconductor device (100) comprises an isolation structure (104). A first active area (108), a protection area (112), and a second active area (116) are formed on the isolation structure (104). A first trench isolation structure (110) electrically separates the first active area (108) and the protection area (112). A second trench isolation structure (114) electrically separates the protection area (112) and the second active area (116). A protection structure (118) is formed in the protection area (112). A first pin (120) of the protection structure (118) is electrically connected to the first active area (108) and a second pin (122) of the protection structure (118) is electrically connected to the second active area (116).

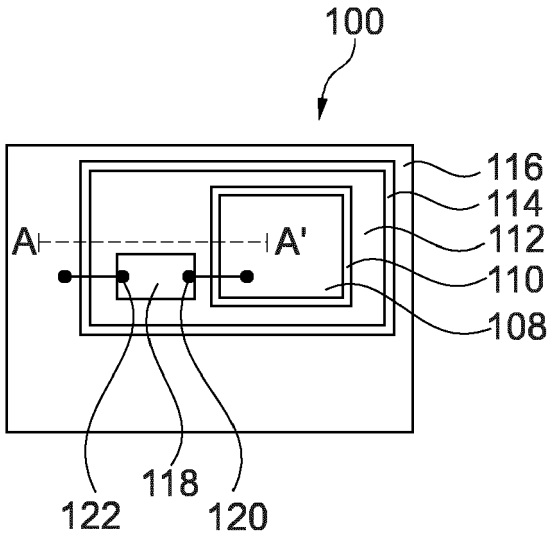

Fig. 1A

EP 3 693 993 A8